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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB857, 2SB858

Silicon PNP Triple Diffused

RENESAS

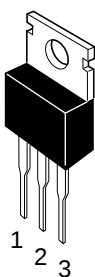
ADE-208-859 (Z)
1st. Edition
September 2000

Application

Low frequency power amplifier complementary pair with 2SD1133 and 2SD1134

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

Item	Symbol	Ratings		Unit
		2SB857	2SB858	
Collector to base voltage	V_{CBO}	-70	-70	V
Collector to emitter voltage	V_{CEO}	-50	-60	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_{C}	-4	-4	A
Collector peak current	$I_{\text{C(peak)}}$	-8	-8	A
Collector power dissipation	P_{C}^{*1}	40	40	W
Junction temperature	T_{j}	150	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-45 to +150	-45 to +150	$^{\circ}\text{C}$

Note: 1. Value at $T_{\text{C}} = 25^{\circ}\text{C}$

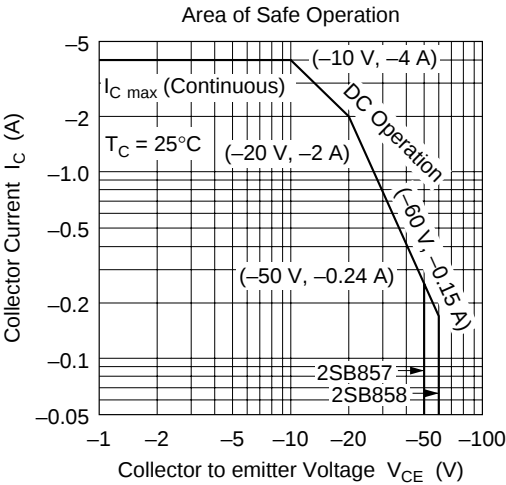
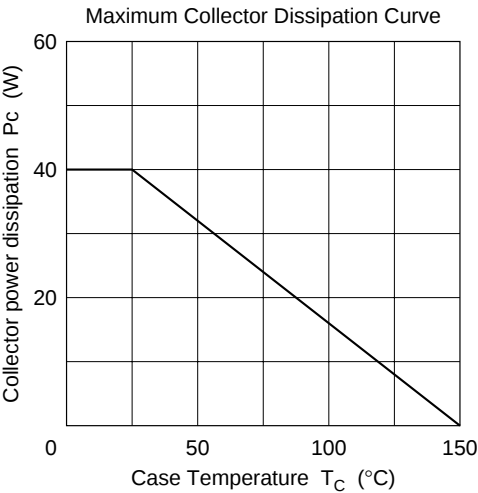
2SB857, 2SB858

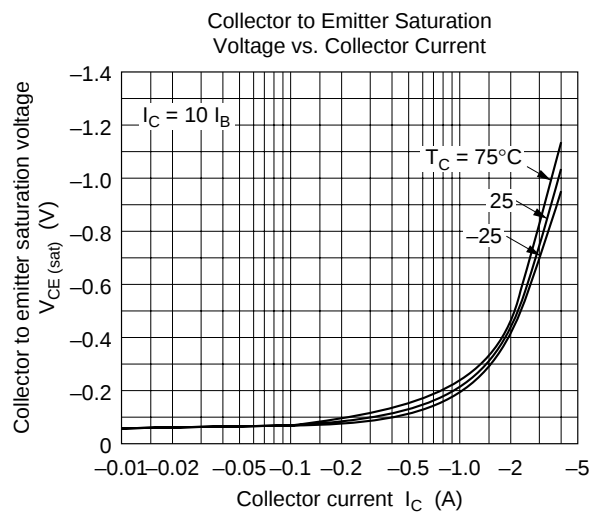
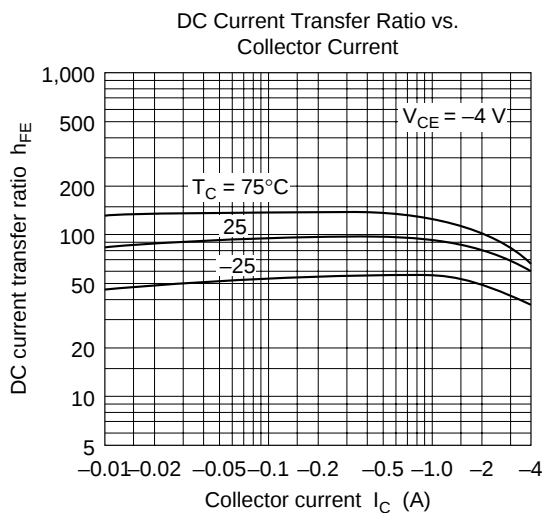
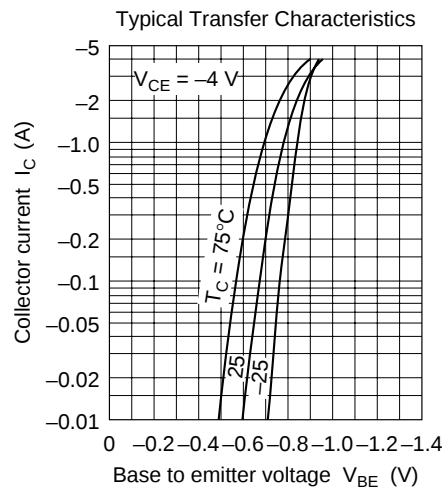
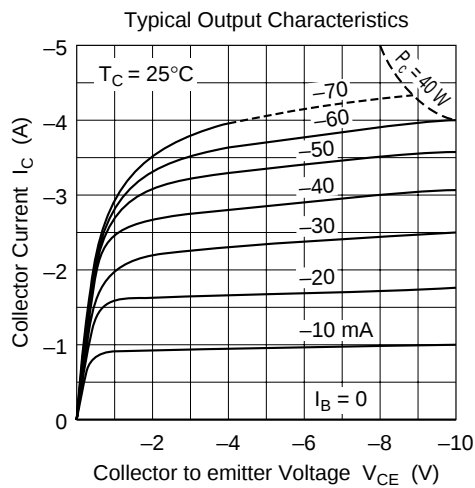
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SB857			2SB858			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	-70	—	—	V	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	-60	—	—	V	$I_C = -50\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	—	—	-1	μA	$V_{CB} = -50\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	320		$V_{CE} =$ $I_C = -1\text{ A}^{*2}$
	h_{FE2}	35	—	—	35	—	—		-4 V $I_C = -0.1\text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -2\text{ A}$, $I_B = -0.2\text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1	—	—	-1	V	$V_{CE} = -4\text{ V}$, $I_C = -1\text{ A}^{*2}$
Gain bandwidth product	f_T	—	15	—	—	15	—	MHz	$V_{CE} = -4\text{ V}$, $I_C = -0.5\text{ A}^{*2}$

Notes: 1. The 2SB857 and 2SB858 are grouped by h_{FE1} as follows.
2. Pulse test

B	C	D
60 to 120	100 to 200	160 to 320





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